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2601/106

**ELECTRICAL MEASUREMENTS  
AND ANALOGUE ELECTRONICS**

**Oct./Nov. 2011**

**Time: 3 hours**



**THE KENYA NATIONAL EXAMINATIONS COUNCIL**

**DIPLOMA IN ELECTRICAL AND ELECTRONICS ENGINEERING  
(POWER OPTION)  
MODULE I**

**ELECTRICAL MEASUREMENTS AND ANALOGUE ELECTRONICS**

**3 hours**

**INSTRUCTIONS TO CANDIDATES**

*You should have the following for this examination.*

*Answer booklet;*

*Drawing instruments;*

*Scientific calculator/mathematical tables.*

*This paper consists of **TWO** sections A and B.*

*Answer any **THREE** questions from section A and **TWO** questions from section B.*

*All questions carry equal marks.*

*Maximum marks for each part of a question are as shown.*

**This paper consists of 5 printed pages.**

**Candidates should check the question paper to ascertain that  
all the pages are printed as indicated and that no questions are missing.**

## SECTION A

Answer any **THREE** questions from this section.

1. (a) State the SI unit of measure for the following quantities:

- (i) Length;
- (ii) Time;
- (iii) Volume;
- (iv) Mass.

(2 marks)

(b) Describe the following types of instrumental errors:

- (i) observational;
- (ii) random.

(8 marks)

(c) (i) A voltmeter having a sensitivity of  $1000\Omega/V$  reads  $100V$  on its  $150V$  scale when connected across an unknown resistor in series with a milliammeter. If the milliammeter reads  $5mA$ , determine:

- I. Apparent resistance of the unknown resistor;
- II. Actual resistance of the unknown resistor;
- III. Error due to the loading effect of the voltmeter.

(ii) The value of unknown resistance of a wheatstone bridge is given by:

$$R_x = \frac{R_2 R_3}{R_1} \quad \text{If } R_1 = 100 \pm 0.5\% \Omega$$

$R_2 = 1000 \pm 0.5\% \Omega$ , and  $R_3 = 840 \pm 0.5\% \Omega$ , determine:

- I — Magnitude of the unknown resistance.
- II — Limiting error; for the unknown resistance.

(10 marks)

2. (a) State "Hall effect" with reference to magnetism.

(2 marks)

(b) With the aid of a diagram, explain how a fluxmeter is used to measure flux density and hence derive the flux density equation.

(12 marks)

(c) With the aid of a circuit diagram, explain how inductance is measured using Maxwell's inductance - capacitance Bridge.

(6 marks)

$$\frac{1}{325} \times 100$$

$$\frac{325}{100}$$

$$\frac{325 \times 100}{100} = 32.8\%$$

$$\frac{325}{100} =$$

$$\frac{20-30}{150}$$

3. (a) With the aid of diagrams, explain the following faults with reference to electrical circuits.

- (i) open circuit;
- (ii) short circuit.

(4 marks)

(b) Distinguish between operation and maintenance manuals as refers to electrical machines.

(4 marks)

(c) Explain the following maintenance principles:

- (i) scheduled maintenance;
- (ii) preventive maintenance;
- (iii) corrective maintenance.

(10 marks)

(d) Explain how faults can be identified on a PCB (Printed Circuit Board)

(2 marks)

(a) (i) Define the following terms with reference to systems:

- I. Reliability; - Ability of a component in a system to perform its function.
- II. Failure. - Inability of a component to perform its function.

(ii) Explain four causes of failure.

(6 marks)

(b) Explain the following reliability indices:

- (i) Mean time between failure; - the measure of average time a component will operate before failure.
- (ii) Mean time to failure; - measure of the time a component will be in operation before failure.
- (iii) Maintainability; - the measure of the ease with which a component can be replaced or repaired.
- (iv) Availability; - the presence of accessibility of a component to perform its function.

(8 marks)

(c) With the aid of a diagram, explain failure periods.

(4 marks)

(d) The MTBF of a certain equipment is 500-hours. Determine the probability of failure of a similar equipment in:

- (i) 100 - hours of life;
- (ii) 1000 - hours of life.

(2 marks)

$R = e^{-t/m}$

$F = 1 - R$   
 $= 1 - e^{-t/m}$

$R = e^{-100/500}$   
 $= e^{-0.2}$

$F = 1 - R$   
 $= 1 - e^{-0.2}$   
 $= 1 - 0.8187$   
 $= 0.1813$

$R = e^{-1000/500}$   
 $= e^{-2}$   
 $= 0.1353$

$1000/130 = 7.69$   
 $130 \times 7.69 = 1000$

$130 \times 7.69 = 1000$

$150 \times 7.69 = 1153.5$   
 $1153.5 - 1000 = 153.5$

$150 \times 7.69 = 1153.5$   
 $1153.5 - 1000 = 153.5$

$26150/30 = 871.67$

2521/105  
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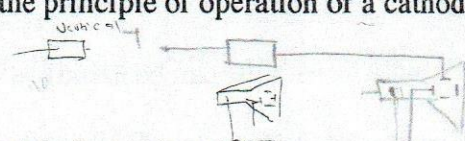
SECTION B

Answer any TWO questions from this section.

5. (a) (i) Define the following terms:  
 I. Proton;  $\rightarrow$  It is positive Electrons in an atom.  
 II. Neutron.  $\rightarrow$  It is Negative Electrons in an atom.

(ii) Distinguish between excited and ionized atoms. (6 marks)

(b) With the aid of a diagram, explain the principle of operation of a cathode ray osalloscope. (14 marks)

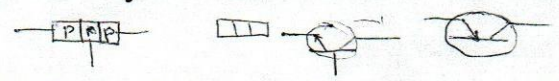


6. (a) Distinguish between intrinsic and extrinsic semiconductor. (4 marks)  
 intr  $\rightarrow$  is current in pure semi-conductor that is small and has be the pure  
 4 atom 4 free electron and holes going opposite direction.

(b) With the aid of a labelled circuit diagrams, explain forward and reverse bias of a PN Junction diode. (16 marks)



7. (a) With the aid of symbols differentiate between PNP and NPN transistors: (6 marks)



(b) With aid of a circuit diagram, derive currents relationship in a common emitter PNP configuration. (12 marks)

$$I_C = I_E \quad I_C = \alpha I_B \quad \alpha = \frac{I_C}{I_E}$$

$$I_E = I_C + I_B$$

(c) The following currents were obtained in a transistor connected in Common Base (CB) configuration:

$I_E = 2\text{mA}$ ,  $I_B = 20\text{mA}$ . Determine the values of  $\alpha$  and  $I_C$  (2 marks)

Handwritten notes and diagrams:

- Diagram of PNP and NPN transistors with labels: PNP, NPN, P, N, P, N, P, N, P.
- Equation:  $I_C = I_E + I_B$
- Text: "Proton  $\rightarrow$  +ve charges of an atom", "Neutron  $\rightarrow$  -ve charges of an atom", "Proton + electron = Neutron".
- Equation:  $\alpha = \frac{I_C}{I_E}$
- Equation:  $\frac{I_C}{I_E} = \alpha$
- Equation:  $I_C = \beta I_B$
- Text: "Proton + electron - electron"

8. (a) State four advantages of FETS (Field Effect Transistors). (4 marks)

low temp coeff  
high sensitivity  
small size, high efficacy  
low power

(b) Figure 1 shows a common drain JFET Amplifier. If  $r_d = 100k\Omega$ ,  $g_m = 300\mu s$  and  $R_L = 10k\Omega$ , determine:

- (i) voltage gain;  $=$   
 (ii) output resistance.  $r_d = V_{cb}$

$g_m = g_{m0} (1 - \frac{V_{GS}}{V_{GS(off)}})$   
 $h_{ie} g_{m0} = \frac{2 I_{DSS}}{V_{GS(off)}}$

$V_e = \frac{V_{GS}}{I_D}$

$g_m = g_{fs} = r_d + R_L$   
 $g_f = 100 + 10 = 110k\Omega$

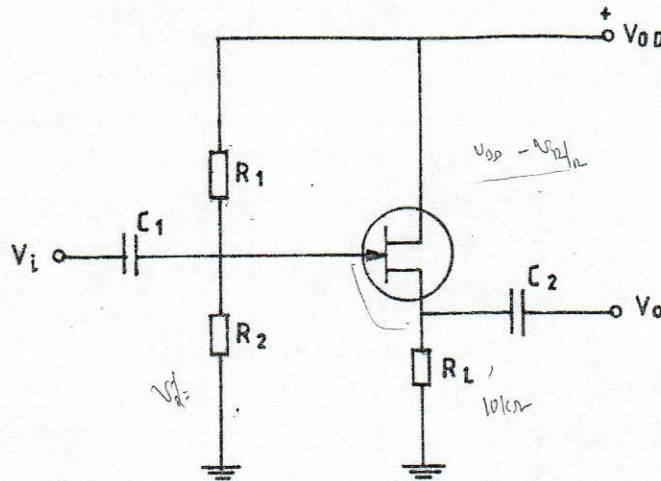


Fig.1

(c) With the aid of a labelled diagram, explain the operation of a  $\Pi$  - filter. (5 marks)



(d) With the aid of a labelled diagram, explain the operation of a Zener diode shunt regulator and derive the expression for the regulator resistance. (7 marks)

$V_s = \text{forward diode}$

$\frac{R_1 R_2}{R_2}$

Voltage gain =  $\left( \frac{R_1 R_2}{R_2 + R_1} \right) R_1$



$R = \frac{V}{I} = \frac{20 - 23.17}{13.0}$

$\frac{V_{GS}}{R} = \frac{V_{GS}}{R} + I_{DSS}$